

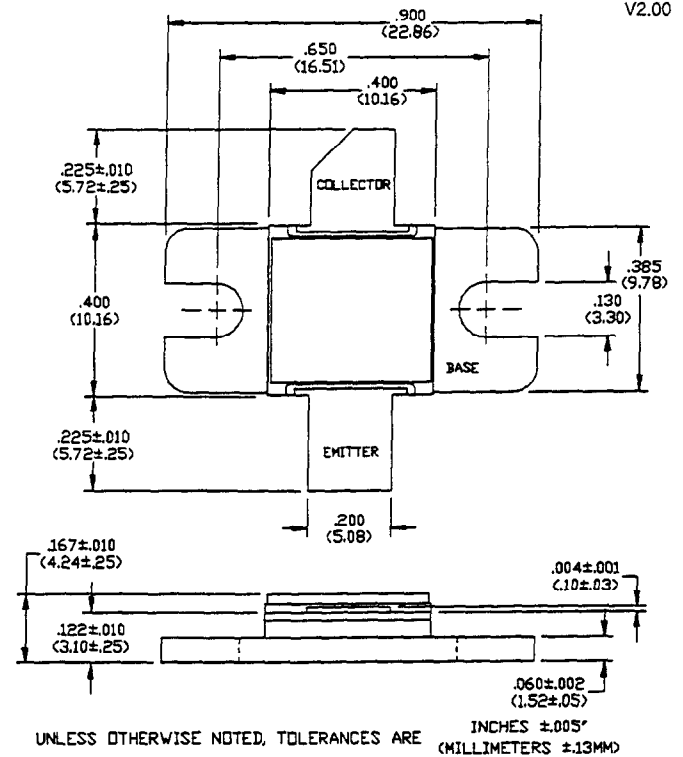
# Radar Pulsed Power Transistor, 65W, 100 $\mu$ s Pulse, 10% Duty 3.1 - 3.4 GHz PH3134-65M

## Features

- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Broadband Class C Operation
- High Efficiency Interdigitated Geometry
- Diffused Emitter Ballasting Resistors
- Gold Metalization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package

## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	65	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	$I_C$	7.7	A
Total Power Dissipation	$P_{TOT}$	350	W
Junction Temperature	$T_J$	200	°C
Storage Temperature	$T_{STG}$	-65 to +200	°C

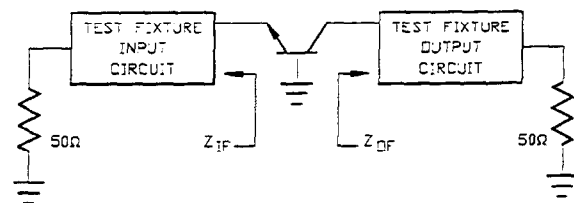


## Electrical Characteristics at 25°C

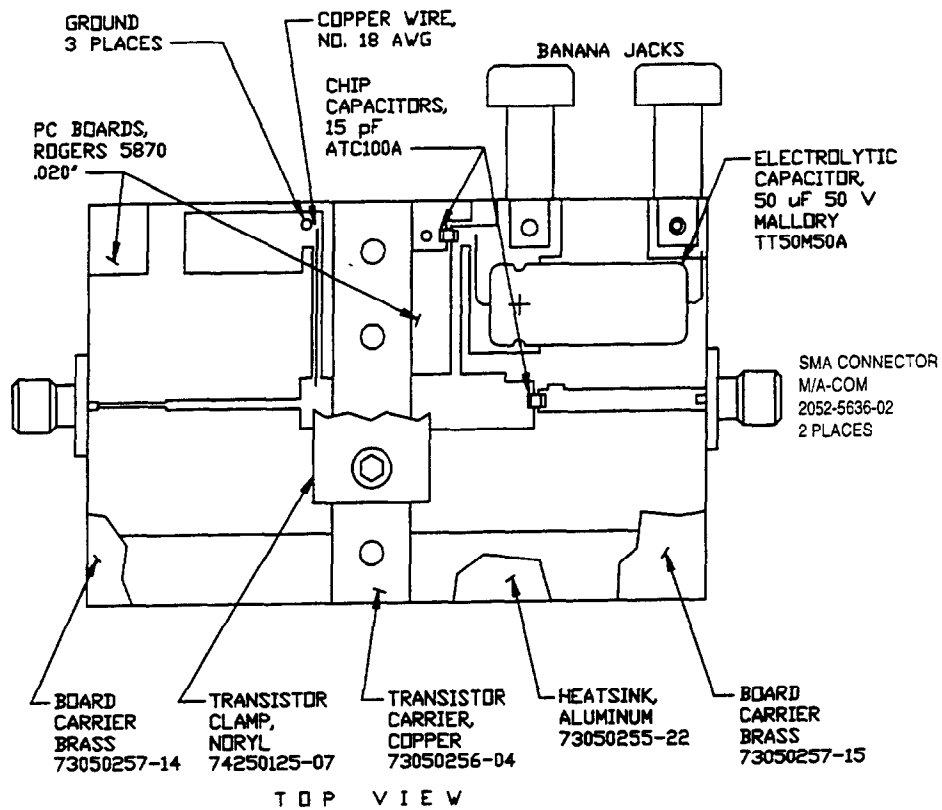
Parameter	Symbol	Min	Max	Units	Test Conditions
Collector-Emitter Breakdown Voltage	$BV_{CES}$	65	-	V	$I_C=25$ mA
Collector-Emitter Leakage Current	$I_{CES}$	-	5.0	mA	$V_{CE}=36$ V
Thermal Resistance	$R_{TH(JC)}$	-	0.5	°C/W	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=3.10, 3.25, 3.40$ GHz
Input Power	$P_{IN}$	-	11.6	W	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=3.10, 3.25, 3.40$ GHz
Power Gain	$G_p$	7.5	-	dB	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=3.10, 3.25, 3.40$ GHz
Collector Efficiency	$\eta_c$	35	-	%	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=3.10, 3.25, 3.40$ GHz
Input Return Loss	RL	6	-	dB	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=3.10, 3.25, 3.40$ GHz
Load Mismatch Tolerance	VSWR-T	-	2:1	-	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=3.25$ GHz

## Broadband Test Fixture Impedances

F(GHz)	$Z_{IF}(\Omega)$	$Z_{OF}(\Omega)$
3.10	11.2 - j11.7	8.1 - j5.3
3.25	11.5 - j9.5	7.1 - j4.3
3.40	12.7 - j7.6	6.4 - j3.3



RF Test Fixture



Test Fixture PC Board Dimensions

